



450V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	I _D T _C = +25°C
-450V	4.9Ω @ V _{GS} = -10V	-4.6A

Description

This MOSFET is designed to minimize the on-state resistance yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features

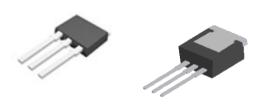
- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

 https://www.diodes.com/quality/product-definitions/

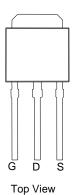
Mechanical Data

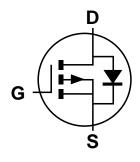
- Case: TO251
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 [®]
- Weight: 0.33 grams (Approximate)











Internal Schematic

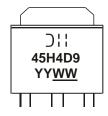
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP45H4D9HJ3	TO251 (Type TH)	75 Pieces / Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



☐ ☐ H = Manufacturer's Marking 45H4D9 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 20 = 2020) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	-450	V
Gate-Source Voltage			V_{GSS}	±30	V
Continuous Drain Current (Note 5) V _{GS} = -10V	Steady State	T _C = +25°C T _C = +100°C	lo	-4.6 -3.0	А
Maximum Body Diode Forward Current (Note 5)			Is	-3.0	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-22.4	Α
Avalanche Current, L = 60mH (Note 7)			las	-2.5	Α
Avalanche Energy, L = 60mH (Note 7)			Eas	187	mJ
Peak Diode Recovery dv/dt (V _{DD} = -400V, I _D = -2.0A)			dv/dt	50	V/ns

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Dawar Dissipation (Note 5)	Tc = +25°C	D-	104	W	
Total Power Dissipation (Note 5)	Tc = +100°C	PD	41	VV	
Thermal Resistance, Junction to Ambient (Note 6)	RθJA	40	°C/W		
Thermal Resistance, Junction to Case (Note 5)	R _θ JC	1.2			
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BVDSS	-450		_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}			-1	μΑ	$V_{DS} = -450V, V_{GS} = 0V$	
Gate-Source Leakage	Igss			±100	nA	$V_{GS} = \pm 30V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	-3.0	-4.0	-5.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
Static Drain-Source On-Resistance	RDS(ON)		3.1	4.9	Ω	$V_{GS} = -10V, I_{D} = -1.05A$	
Diode Forward Voltage	V_{SD}			-1.3	V	$V_{GS} = 0V$, $I_{S} = -2.1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss		547	_		V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	74	_	pF		
Reverse Transfer Capacitance	Crss	_	3.1	_			
Total Gate Charge (V _{GS} = -10V)	Qg	_	13.7	_			
Gate-Source Charge	Qgs	_	3.4	_	nC	$V_{DS} = -360V$, $I_{D} = -2.7A$, $V_{GS} = -10V$	
Gate-Drain Charge	Q_{gd}	_	6.0	_			
Turn-On Delay Time	tD(ON)	_	19	_		$V_{DD} = -225V$, $R_G = 3.0\Omega$, $I_D = -2.7A$	
Turn-On Rise Time	t _R	_	40	_			
Turn-Off Delay Time	tD(OFF)	_	32	_	ns		
Turn-Off Fall Time	tF		31	_			
Body Diode Reverse Recovery Time	t _{RR}	_	164	_	ns	V _G S = 0V, V _{DD} = -200V, I _S = -2.7A,	
Body Diode Reverse Recovery Charge	Q _{RR}		1.3	_	nC	dl/dt = 100A/µs	

Notes:

- 5. Device mounted on infinite heatsink.
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 Guaranteed by design. Not subject to production testing.
 Short duration pulse test used to minimize self-heating effect.



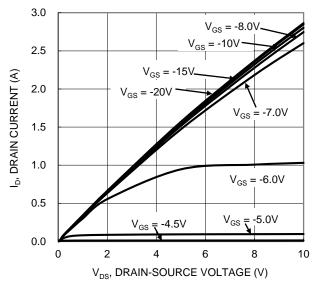


Figure 1. Typical Output Characteristic

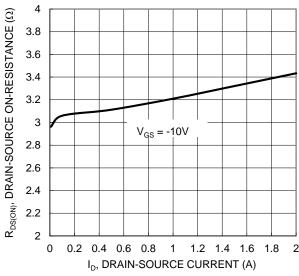


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

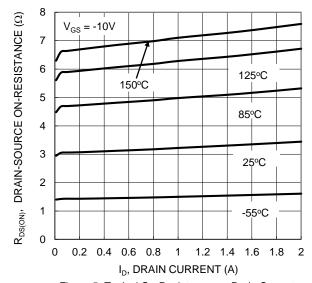


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

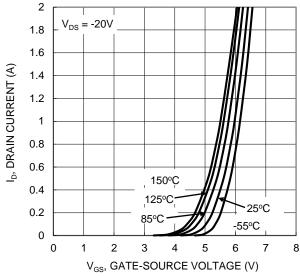


Figure 2. Typical Transfer Characteristic

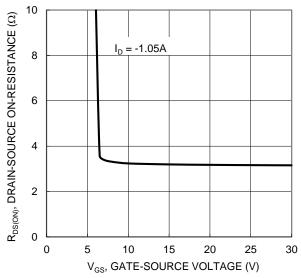


Figure 4. Typical Transfer Characteristic

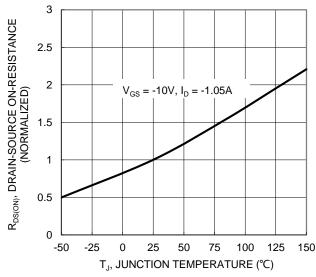


Figure 6. On-Resistance Variation with Temperature



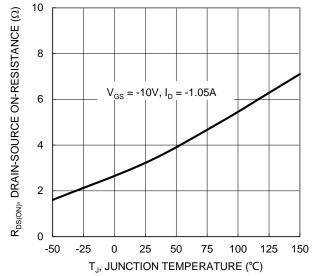
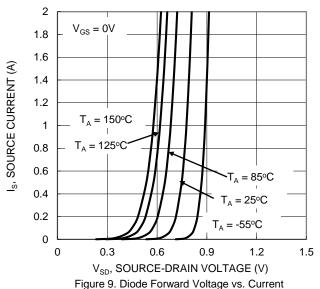


Figure 7. On-Resistance Variation with Temperature



10 8 6 $V_{DS} = -360V, I_{D} = -2.7A$ $V_{GS}(V)$ 4 2 0 0 2 8 10 12 14 Q_g (nC) Figure 11. Gate Charge

5 $V_{GS(TH)}, \text{ GATE THRESHOLD VOLTAGE (V)}$ 4.5 $I_D = -1mA$ 4 $I_{D} = -250 \mu A$ 3.5 3 2.5 2 -50 -25 0 25 50 75 100 125 150 T_J, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature

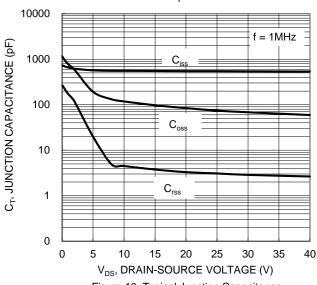


Figure 10. Typical Junction Capacitance

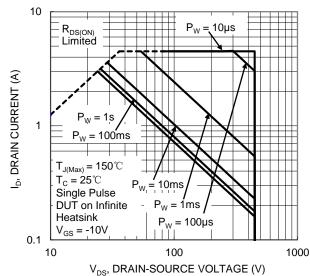


Figure 12. SOA, Safe Operation Area



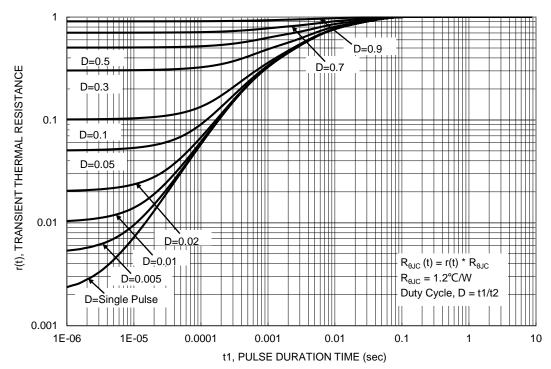


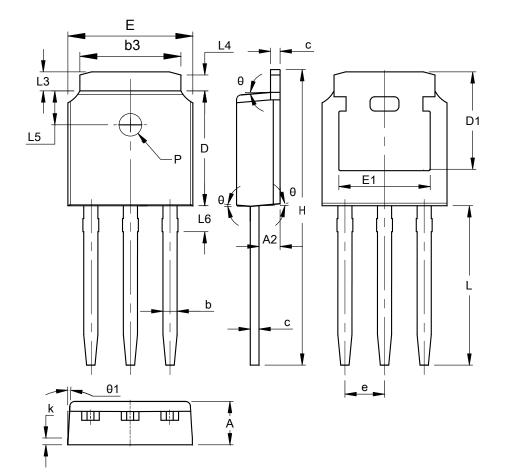
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO251 (Type TH)



TO251 (Type TH)						
Dim	Min	Max	Тур			
Α	2.20	2.40	2.30			
A2	0.97	1.17	1.07			
b	0.68	0.90	0.78			
b3	5.20	5.50	5.33			
С	0.43	0.63	0.53			
D	5.98	6.22	6.10			
D1	5	.30 RE	F			
е	2.	286 BS	C			
Е	6.40	6.80	6.60			
E1	4.63	5.03	4.83			
Н	16.22	16.82	16.52			
k	().40REI	-			
L	9.15	9.65	9.40			
L3	0.88	1.28	1.02			
L4	0.75 REF					
L5	1.65	1.95	1.80			
L6	0.85	1.25	1.05			
PØ	1.20					
θ	5°	9°	7°			
θ1	5°	9°	7°			
All Dimensions in mm						



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